**Product data sheet** 

# 1. General description

Hyperfast power diode in a 2-lead IITO220 plastic package.

### 2. Features and benefits

- · Isolated plastic package
- Low leakage current
- · Low reverse recovery current
- Low thermal resistance
- · Reduces switching losses in associated MOSFET or IGBT

## 3. Applications

- Active PFC in air conditioner
- High frequency switched-mode power supplies
- Continuous Current Mode (CCM) Power Factor Correction (PFC)

### 4. Quick reference data

Table 1. Quick reference data

| Symbol           | Parameter                           | ameter Conditions Values   |            |     | Unit |     |      |
|------------------|-------------------------------------|--|------------|-----|------|-----|------|
| Absolute         | maximum rating                      |  |            |     |      |     |      |
| $V_{RRM}$        | repetitive peak reverse voltage     |  | 600        |     |      |     | V    |
| $I_{F(AV)}$      | average forward current             | $\delta$ = 0.5; T <sub>mb</sub> $\leq$ 90 °C; square-wave pulse Fig. 1; Fig. 2; Fig. 3                             | 30         |     |      | А   |      |
| I <sub>FRM</sub> | repetitive peak forward current     | $\delta$ = 0.5; t <sub>p</sub> = 25 μs; T <sub>mb</sub> ≤ 90 °C; square-wave pulse                                 | 60         |     |      | А   |      |
| I <sub>FSM</sub> | non-repetitive peak forward current | $t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse;<br>Fig. 4   |            |     |      | А   |      |
|                  |                                     | $t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse   |            |     |      | А   |      |
| Symbol           | Parameter                           | Conditions   |            | Min | Тур  | Max | Unit |
| Static ch        | aracteristics                       |  |            | ,   |      |     |      |
| V <sub>F</sub>   | forward voltage                     | I <sub>F</sub> = 30 A; T <sub>j</sub> = 150 °C; <u>Fig. 6</u>  | - 1.38 1.8 |     | 1.8  | V   |      |
| Dynamic          | characteristics                     |  |            | ,   | ,    |     |      |
| t <sub>rr</sub>  | reverse recovery time               | $I_F = 1 \text{ A}$ ; $V_R = 30 \text{ V}$ ; $dI_F/dt = 50 \text{ A}/\mu\text{s}$ ; $T_j = 25 \text{ °C}$ ; Fig. 7 |            | -   | -    | 35  | ns   |

# 5. Pinning information

### **Table 2. Pinning information**

| Pin | Symbol | Description             | Simplified outline       | Graphic symbol     |
|-----|--------|-------------------------|--------------------------|--------------------|
| 1   | K      | cathode                 |                          |                    |
| 2   | A      | anode                   |                          | K — A<br>001aaa020 |
| mb  | n.c.   | mounting base; isolated |                          | 001aaa020          |
|     |        |                         |                          |                    |
|     |        |                         |                          |                    |
|     |        |                         |                          |                    |
|     |        |                         | U U<br>1 2<br>IITO220-2L |                    |

# 6. Ordering information

### **Table 3. Ordering information**

| Type number | Package<br>Name | Orderable part number | Packing method | Small packing quantity | Package version | Package issue date |
|-------------|-----------------|-----------------------|----------------|------------------------|-----------------|--------------------|
| BYC30Y-600P | IITO220-2L      | BYC30Y-600PQ          | Tube           | 50                     | IITO220E-2L     | 03-Mar-2020        |

# 7. Marking

#### Table 4. Marking codes

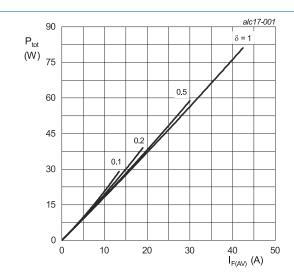
| Type number | Marking codes |
|-------------|---------------|
| BYC30Y-600P | BYC30Y        |
|             | 600P          |

# 8. Limiting values

### **Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol           | Parameter                           | Conditions   | Values     | Unit |
|------------------|-------------------------------------|--|------------|------|
| $V_{RRM}$        | repetitive peak reverse voltage     |  | 600        | V    |
| $V_{RWM}$        | crest working reverse voltage       |  | 600        | V    |
| $V_R$            | reverse voltage                     | DC   | 600        | V    |
| $I_{F(AV)}$      | average forward current             | $δ = 0.5$ ; $T_{mb} \le 90$ °C; square-wave pulse;<br>Fig. 1; Fig. 2; Fig. 3 | 30         | А    |
| I <sub>FRM</sub> | repetitive peak forward current     | $δ = 0.5$ ; $t_p = 25 \mu s$ ; $T_{mb} \le 90 °C$ ; square-wave pulse        | 60         | А    |
| I <sub>FSM</sub> | non-repetitive peak forward current | $t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse;<br>Fig. 4             | 200        | А    |
|                  |                                     | $t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse                       | 220        | А    |
| T <sub>stg</sub> | storage temperature                 |  | -65 to 175 | °C   |
| T <sub>j</sub>   | junction temperature                |  | 175        | °C   |



$$\begin{split} I_{\text{F(AV)}} &= I_{\text{F(RMS)}} \times \sqrt{\delta} \\ V_{\text{o}} &= 1.797 \text{ V; } R_{\text{s}} = 0.0027 \text{ } \Omega \end{split}$$

Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values

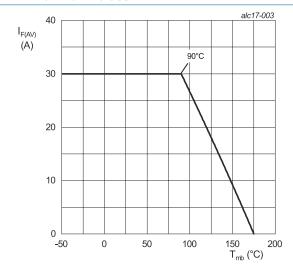
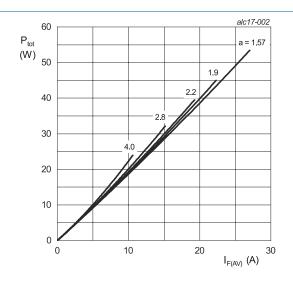


Fig. 3. Forward current as a function of mounting base temperature; maximum values



a = form factor =  $I_{F(RMS)}/I_{F(AV)}$  $V_o$  = 1.797 V;  $R_s$  = 0.0027  $\Omega$ 

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

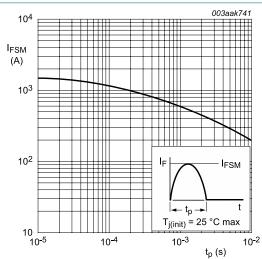
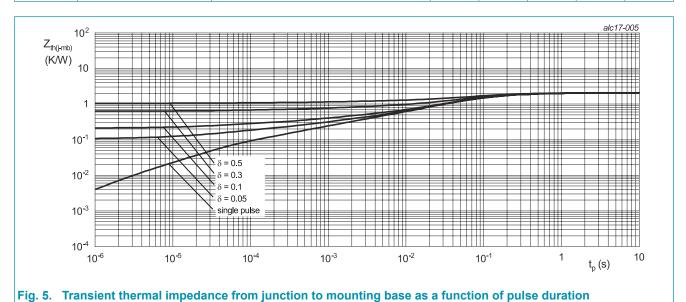


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values

### 9. Thermal characteristics

#### **Table 6. Thermal characteristics**

| Symbol                | Parameter   | Conditions                     | Min | Тур | Max | Unit |
|-----------------------|---|--------------------------------|-----|-----|-----|------|
| R <sub>th(j-mb)</sub> | thermal resistance<br>from junction to<br>mounting base | with heatsink compound; Fig. 5 | -   | -   | 2.1 | K/W  |
| R <sub>th(j-a)</sub>  | thermal resistance<br>from junction to<br>ambient       | in free air                    | -   | 60  | -   | K/W  |



### 10. Isolation characteristics

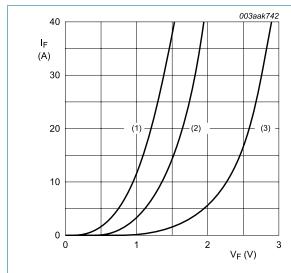
#### **Table 7. Isolation characteristics**

| S  | ymbol     | Parameter             | Conditions  | Min | Тур | Max  | Unit |
|----|-----------|-----------------------|---|-----|-----|------|------|
| Vi | isol(RMS) | RMS isolation voltage | 50 Hz $\leq$ f $\leq$ 60 Hz; RH $\leq$ 65 %; from all pins to external heatsink; sinusoidal waveform; clean and dust free | -   | -   | 2500 | V    |
| C  | isol      | isolation capacitance | f = 1 MHz; from cathode to external heatsink  | -   | 10  | -    | pF   |

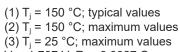
## 11. Characteristics

#### **Table 8. Characteristics**

| Symbol          | Parameter                     | Conditions  | Mi | n Typ | Max  | Unit |
|-----------------|-------------------------------|---|----|-------|------|------|
| Static cha      | racteristics                  |   |    |       |      |      |
| $V_{F}$         | forward voltage               | I <sub>F</sub> = 30A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>   | -  | 2     | 2.75 | V    |
|                 |                               | I <sub>F</sub> = 30 A; T <sub>j</sub> = 150 °C; <u>Fig. 6</u>   | -  | 1.38  | 1.8  | V    |
| I <sub>R</sub>  | reverse current               | V <sub>R</sub> = 600 V; T <sub>j</sub> = 25 °C  | -  | -     | 10   | μA   |
|                 |                               | V <sub>R</sub> = 600 V; T <sub>j</sub> = 150 °C   | -  | -     | 1    | mA   |
| Dynamic         | characteristics               |   |    | '     |      |      |
| Q <sub>r</sub>  | recovered charge              | $I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$<br>$\mu$ s; $T_J = 25 \text{ °C}; Fig. 7$               | -  | 50    | -    | nC   |
|                 |                               | $I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$<br>$\mu$ s; $T_J = 125 ^{\circ}\text{C}; Fig. 7$        | -  | 280   | -    | nC   |
| t <sub>rr</sub> | reverse recovery time         | $I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 50 \text{ A/}\mu\text{s};$<br>$T_j = 25 \text{ °C}; Fig. 7$               | -  | -     | 35   | ns   |
|                 |                               | $I_F = 30 \text{ A}$ ; $V_R = 200 \text{ V}$ ; $dI_F/dt = 200 \text{ A/}\mu\text{s}$ ; $T_j = 25 ^{\circ}\text{C}$ ; Fig. 7 | -  | 35    | -    | ns   |
|                 |                               | $I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$<br>$T_j = 125 \text{ °C}; Fig. 7$           | -  | 70    | -    | ns   |
| I <sub>RM</sub> | peak reverse recovery current | $I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$<br>$T_j = 25 ^{\circ}\text{C}; Fig. 7$      | -  | 3.5   | -    | А    |
|                 |                               | $I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$<br>$T_i = 125 \text{ °C}; Fig. 7$           | -  | 7.6   | -    | А    |



 $V_o = 1.797 \text{ V; } R_s = 0.0027 \Omega$ Fig. 6. Forward current as a function of forward voltage



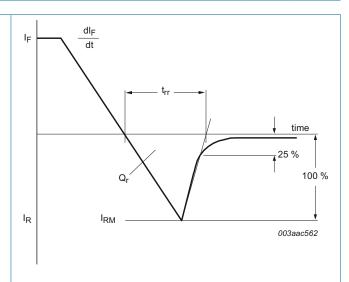
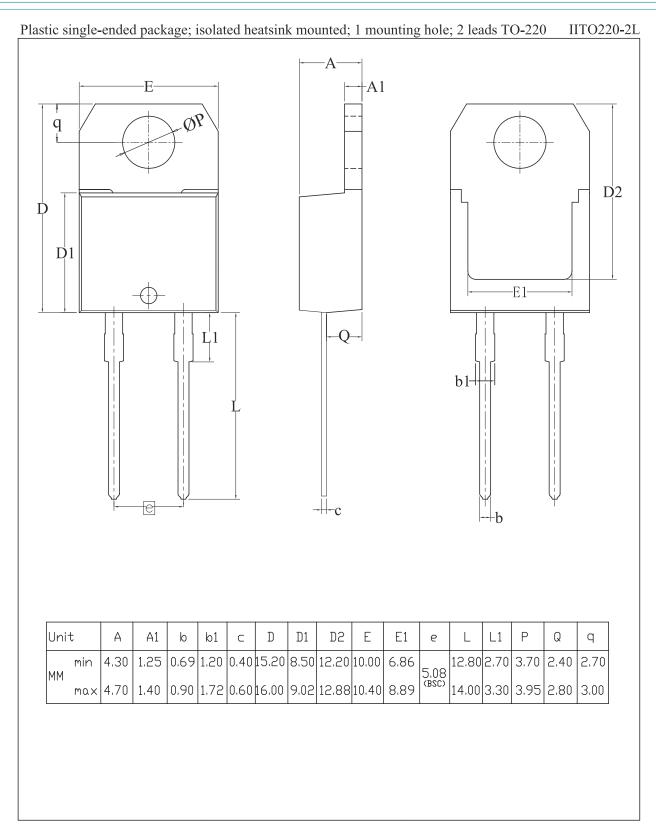


Fig. 7. Reverse recovery definitions; ramp recovery

# 12. Package outline



# 13. Legal information

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| Document status [1][2]               | Product status [3] | Definition  |
|--------------------------------------|--------------------|---|
| Objective<br>[short] data<br>sheet   | Development        | This document contains data from the objective specification for product development. |
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**BYC30Y-600P** 

Hyperfast power diode

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